

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Darlington power transistor)

2SD1631

Micro Motor Drive, Hammer Drive Applications

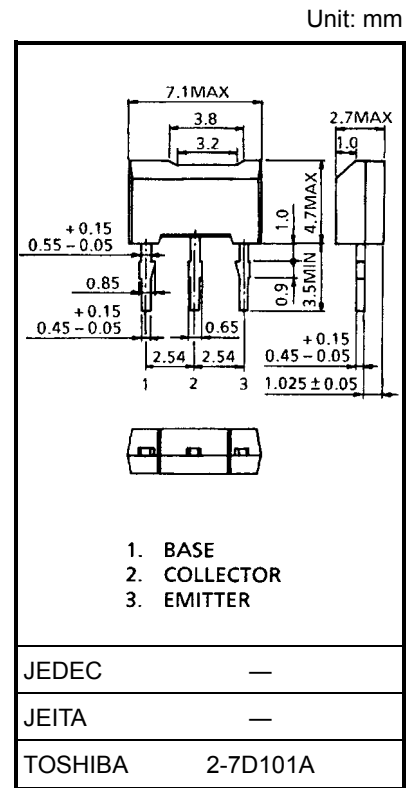
Switching Applications

Power Amplifier Applications

- High DC current gain: $h_{FE} = 4000$ (min) ($V_{CE} = 2\text{ V}$, $I_C = 150\text{ mA}$)
- Low saturation voltage: $V_{CE(sat)} = 1.5\text{ V}$ (max) ($I_C = 1\text{ A}$, $I_B = 1\text{ mA}$)

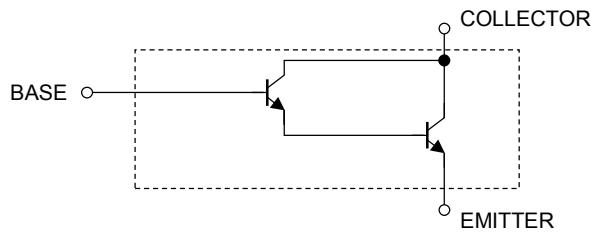
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	10	V
Continuous collector current	I_C	1.5	A
Continuous base current	I_B	50	mA
Collector power dissipation	P_C	1000	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

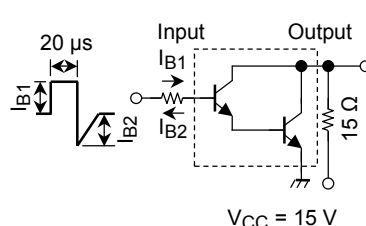


Weight: 0.2 g (typ.)

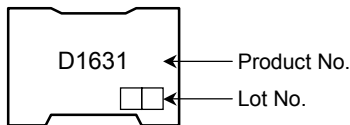
Equivalent Circuit



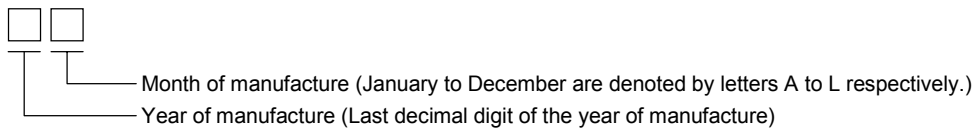
Electrical Characteristics (Ta = 25°C)

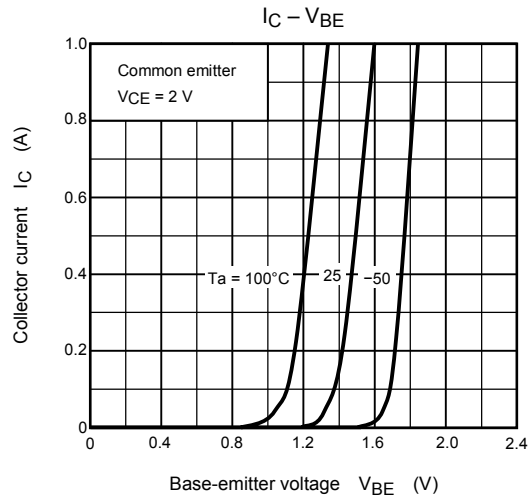
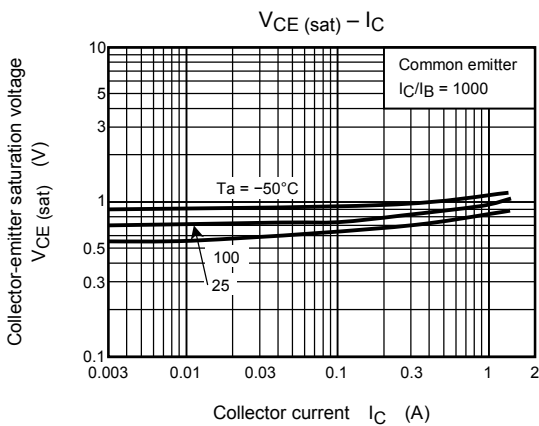
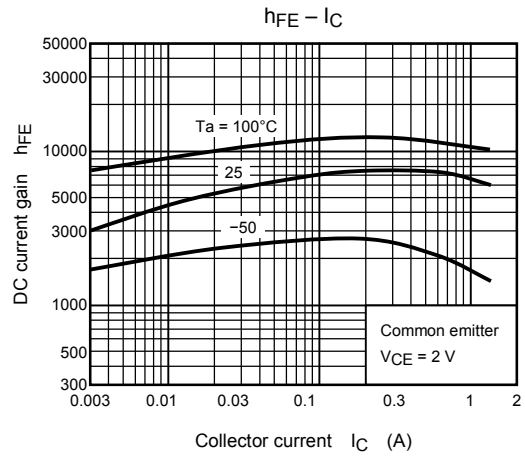
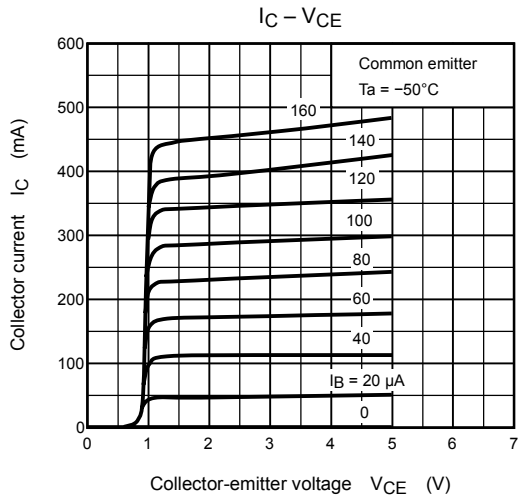
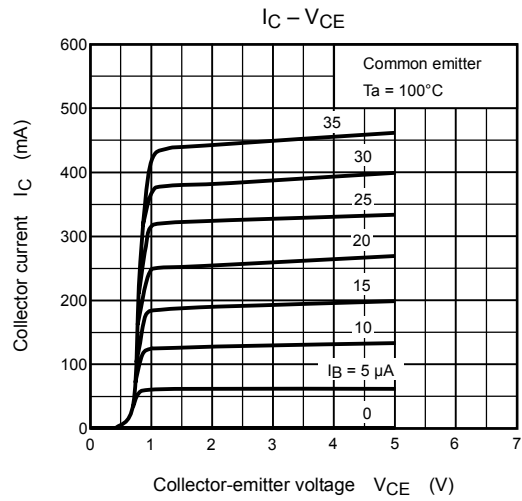
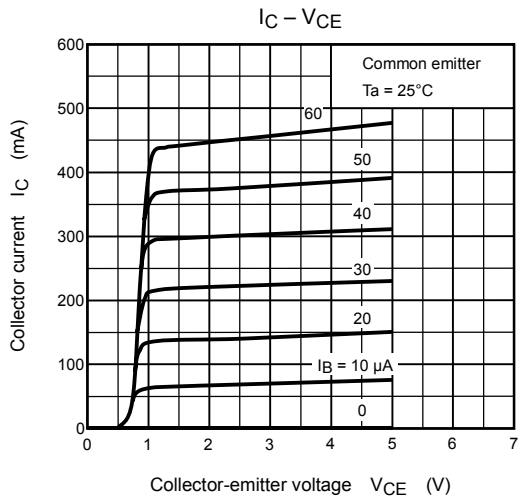
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 30\text{ V}, I_E = 0$	—	—	10	μA
Emitter cut-off current		I_{EBO}	$V_{EB} = 10\text{ V}, I_C = 0$	—	—	10	μA
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	30	—	—	V
DC current gain		h_{FE}	$V_{CE} = 2\text{ V}, I_C = 150\text{ mA}$	4000	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 1\text{ mA}$	—	—	1.5	V
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C = 1\text{ A}, I_B = 1\text{ mA}$	—	—	2.2	V
Switching time	Turn-on time	t_{on}		—	0.20	—	μs
	Storage time	t_{stg}		—	0.6	—	
	Fall time	t_f		$I_{B1} = -I_{B2} = 1\text{ mA}$ $I_C = 1\text{ A}, \text{duty cycle} \leq 1\%$	—	0.3	

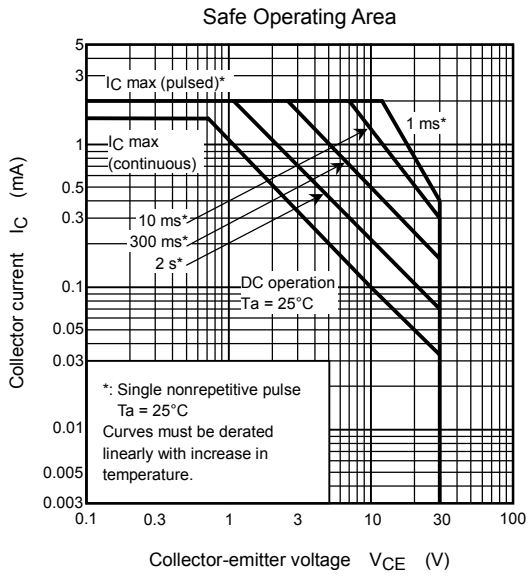
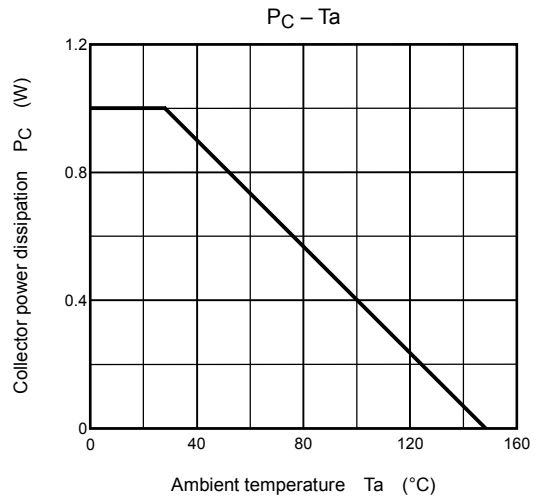
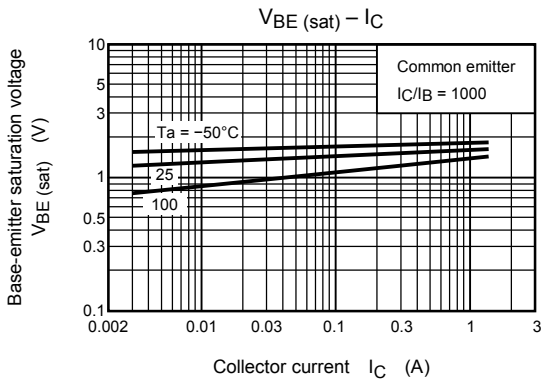
Marking



Explanation of Lot No.







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